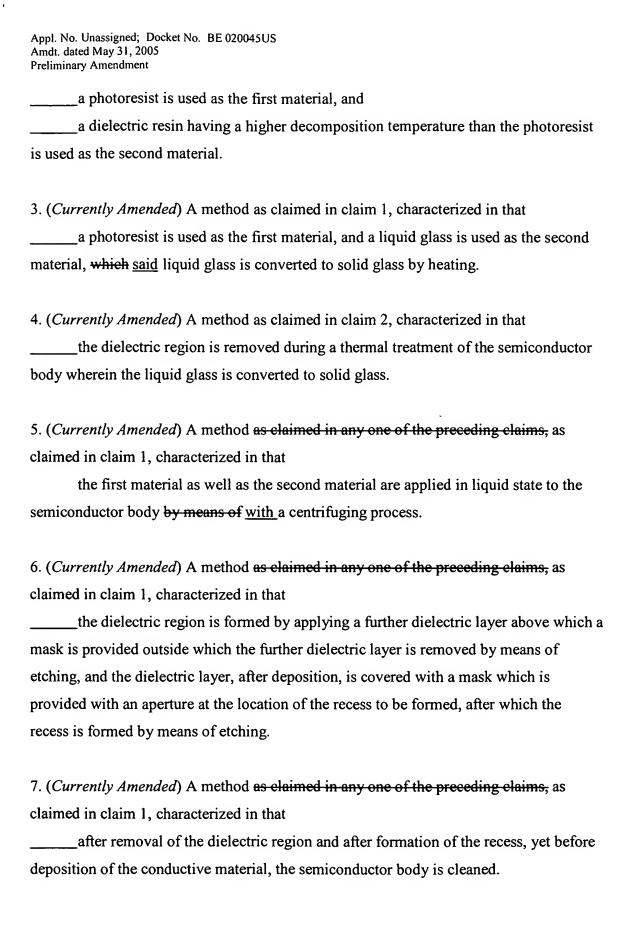
Appl. No. Unassigned; Docket No. BE 020045US Amdt. dated May 31, 2005 Preliminary Amendment

## JC17 Rec'd PCT/PTO 16 JUN 2005

## **Amendments to the Claims**

1. (Currently Amended) A method of manufacturing a semiconductor device with a
semiconductor body and a substrate and comprising,
at least one semiconductor element, which the semiconductor device is equipped
with at least one connection region and
a superjacent strip-shaped connection conductor which is connected to the
connection region,
which the connection region and the superjacent strip-shaped connection
conductor are both recessed in a dielectric, and
a dielectric region of a first material is provided on the semiconductor body at the
location of the connection region to be formed, after which
the dielectric region is coated with a dielectric layer of a second material that
differs from the first material,
which said dielectric layer is provided, at the location of the strip-shaped
connection conductor to be formed, with a strip-shaped recess which, viewed in
projection, overlaps the dielectric region and extends up to said dielectric region,
and after the formation of the strip-shaped recess and the removal of the dielectric
region,
the connection region is formed by depositing an electroconductive material in the
space a space obtained by the removal of the dielectric region, and
the strip-shaped connection conductor is formed by depositing an
electroconductive material in the strip-shaped recess, characterized in that
for the first material use is made of an organic material, and
for the second material use is made of a material having a higher
decomposition temperature than the organic material, and
the dielectric region is removed by heating it at a temperature at a temperature
above the decomposition temperature of the organic material yet below the
decomposition temperature of the second material.

2. (Currently Amended) A method as claimed in claim 1, characterized in that



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8. (Currently Amended) A method as claimed in any one of the preceding claims, as
claimed in claim 1, characterized in that
copper is used as the electroconductive material, and
prior to the deposition of the copper, an electroconductive layer is deposited at the
location of the connection region to be formed, which said electroconductive layer forms
a barrier for copper.
9. (Currently Amended) A method as claimed in claim 8, characterized in that
the electroconductive layer is applied by means of a physical vapor deposition
process, and
the copper is provided by means of an electroplating process.
10. (Currently Amended) A semiconductor device obtained by means of a method as
elaimed in any one of the preceding claims. by the method of claim 1.